

ABSTRACT OF THE DISCLOSURE

A semiconductor manufacturing process that includes providing an insulating material, providing a first photoresist over the insulating material, defining and patterning the first photoresist, anisotropically etching the insulating material to form at least one groove in the insulating material, removing the first photoresist, providing a second photoresist over the insulating material, defining and patterning the second photoresist to form a plurality of tops and sidewalls, depositing a layer of carbon-fluoride material over the tops and sidewalls of the defined and patterned second photoresist, and anisotropically etching the insulating layer to form at least one opening, wherein the at least one opening is aligned with the at least one groove.

20070630-021502

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